■ Features

- High Output Power: Psat=54.0dBm (Typ.)
- High Gain: Gp=10.0dB (Typ.)
- High Power Added Efficiency: PAE=39% (Typ.)
- Frequency Band: 9.3 to 9.5GHz
- Impedance Matched Zin/Zout = 50ohm
- Hermetically Sealed Package

■ Description

The SGC9395-200B-R is a high power GaN-HEMT that is internally matched for X-band radar bands to provide optimum power and gain in a 50ohm system.

ABSOLUTE MAXIMUM RATING (Case Temperature T_c=25 deg.C)

Item	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	55	V
Gate-Source Voltage	V_{GS}	-15	V
Storage Temperature	T_{stg}	-55 to +125	deg.C
Channel Temperature	T_{ch}	+250	deg.C

RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
Drain-Source Voltage	V_{DS}		<=50	V
Forward Gate Current	I_{GF}	Rg=51ohm	<=123.3	mA
Reverse Gate Current	I_{GR}	Rg=51ohm	>=-9.0	mA
Channel Temperature	T_{ch}		<+200	deg.C
Output Power	P_{out}		<=P5dB	dBm

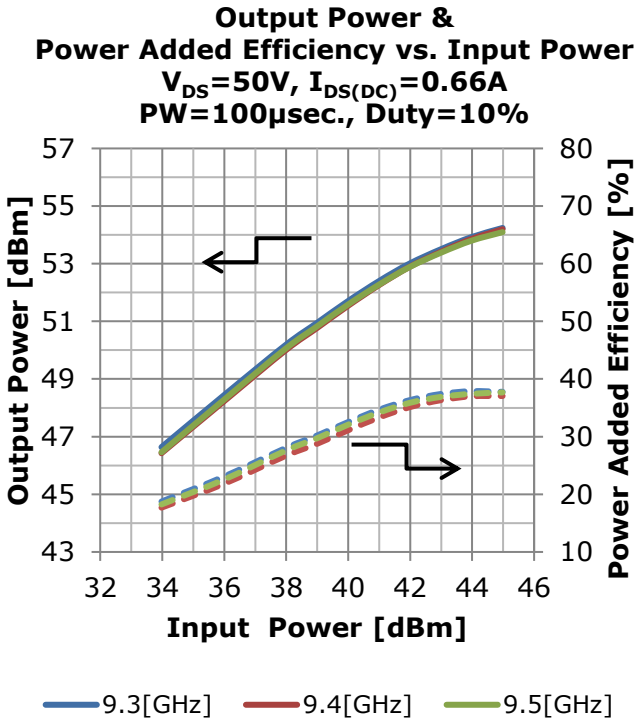
ELECTRICAL CHARACTERISTICS (Case Temperature T_c=25 deg.C)

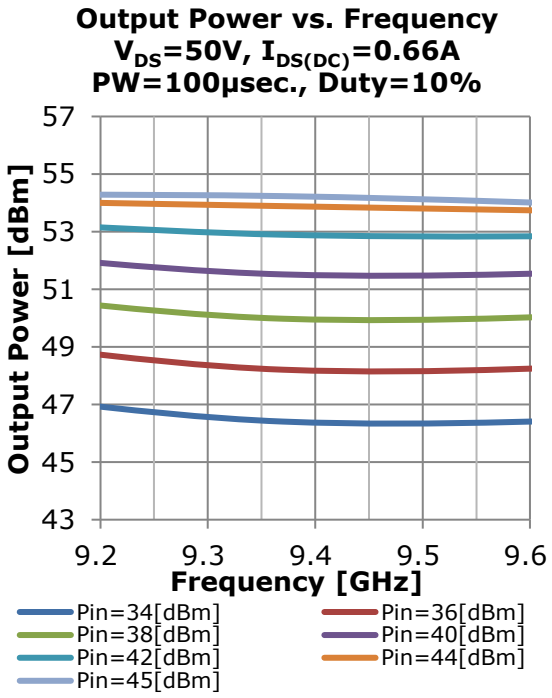
Item	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Pinch-off Voltage	V_p	V_{DS}=50V, I_{DS}=13.0mA	-	-4.5	-	V
Frequency Range	Freq.	V_{DS}=50V-typ. $I_{DS(DC)}$=0.66A-typ. Pulse Width=100µsec. Duty=10%	9.3	-	9.5	GHz
Output Power at Pin=44dBm	P_{sat}		53.0	54.0	-	dBm
Power Gain at Pout=53dBm	G_p		9.0	10.0	-	dB
Drain Current at Pin=44dBm	I_{DSR}		-	11.6	14.5	A
Power Added Efficiency at Pin=44dBm	PAE		-	39	-	%
Gain Flatness	ΔG		-	1.6	-	dB
Thermal Resistance	R_{th}	Channel to Case (P_{diss}=100W,CW)	-	0.6	0.8	deg.C/W

CASE STYLE	IK	
RoHS Compliance	YES	
ESD	Class 2	2000V to <4000V

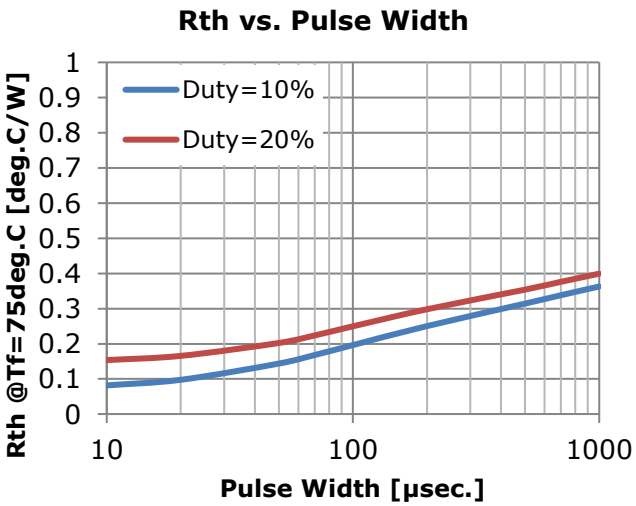
Note: Based on ANSI/ESDA/JEDEC JS-001-2012(C=100pF, R=1.5kohm)

● RF Characteristics



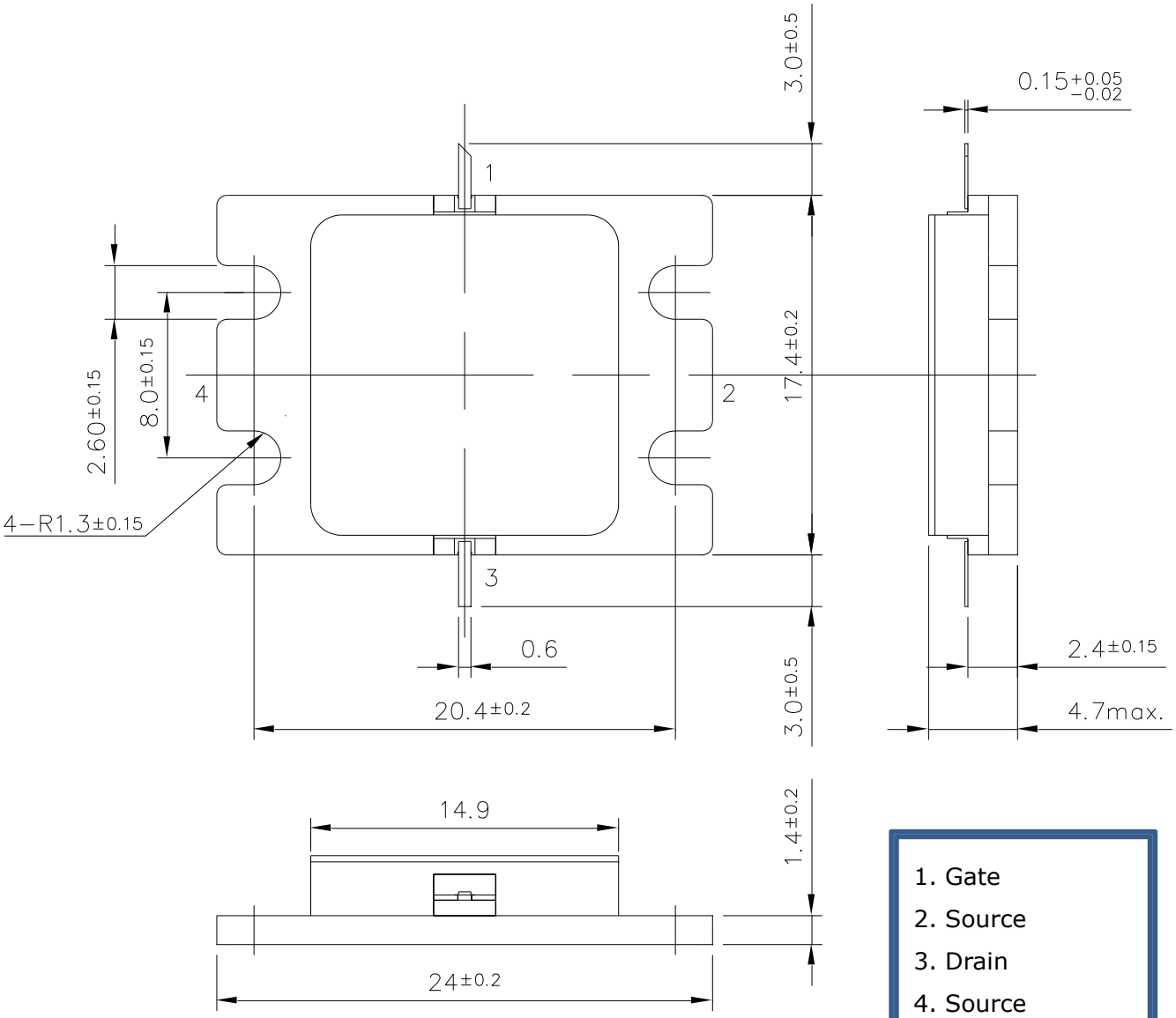


● Thermal Characteristics In Pulsed Operation



● Package Outline

Case Style : IK



1. Gate
2. Source
3. Drain
4. Source

Unit: mm

Tolerance: ±0.15

For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
  This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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